

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of forming a ~~thin~~ film on a base substance via an intermediate layer, comprising the steps of:

calculating an interface energy E_a at an interface A between said base substance and said intermediate layer and an interface energy E_b at an interface B between said intermediate layer and said thin film;

calculating an interface energy E_c at an interface C between said base substance and said thin film in a state where said intermediate layer is omitted; ~~and~~

selecting a substance for said intermediate layer so as to satisfy conditions of in which each of said interface energies E_a and E_b is lower than 2 J/m^2 , $E_a < E_c$ and $E_b < E_c$; and wherein after calculating an energy E_d of a crystal including the interface and an energy E_p of a perfect crystal taking account of chemical potentials of constituent elements by the first-principles calculation band method, each of said interface energies E_a , E_b and E_c is calculated as $E_d - E_p$.

2 – 3. (Cancelled).

4. (Currently Amended) The ~~thin~~ film forming method according to claim 1, wherein in at least one of said interfaces A and B, substances on both sides of the interface share a specific atomic layer contained in common therein, to thereby reduce the interface energy.

5. (Currently Amended) The ~~thin~~ film forming method according to claim 1, wherein at least one of said interfaces A and B has a small difference in crystal lattice constant compared to said interface C, to thereby reduce the interface energy.

6. (Currently Amended) The ~~thin~~ film forming method according to claim 1, wherein said substance for said intermediate layer is an oxide having a stacked-layer structure

containing at least two kinds of atomic layers, wherein one kind of said atomic layers decreases said interface energy E_a compared to said interface energy E_c , and another kind of said atomic layers decreases said interface energy E_b compared to said interface energy E_c .

7. (Currently Amended) The ~~thin~~ film forming method according to claim 1, wherein said substance for said intermediate layer has a crystal structure of a perovskite type.

8. (Currently Amended) The ~~thin~~ film forming method according to claim 6, wherein, when said oxide as said substance for said intermediate layer includes a coordination polyhedron formed of oxygen ions surrounding a metal ion, in at least one of said interfaces A and B, the oxygen ions are also linked with another substance constituting the interface.

9. (Currently Amended) The ~~thin~~ film forming method according to claim 6, wherein said base substance has a crystal structure of a rock-salt type.

10. (Currently Amended) The ~~thin~~ film forming method according to claim 1, wherein said base substance is MgO, said substance for said intermediate layer is BaZrO_3 , and said thin film is $\text{RE}_{1+x}\text{Ba}_{2-x}\text{Cu}_3\text{O}_{7-y}$ where RE represents at least one kind of rare earth elements.

11. (New) The film forming method according to claim 10, wherein each of x and y represents a respective numerical value.

12. (New) The film forming method according to claim 10, wherein x represents a number from 0 to 1, and y represents a number from 0 to 6.